

Silicon PNP Power Transistor

2SA1327

DESCRIPTION

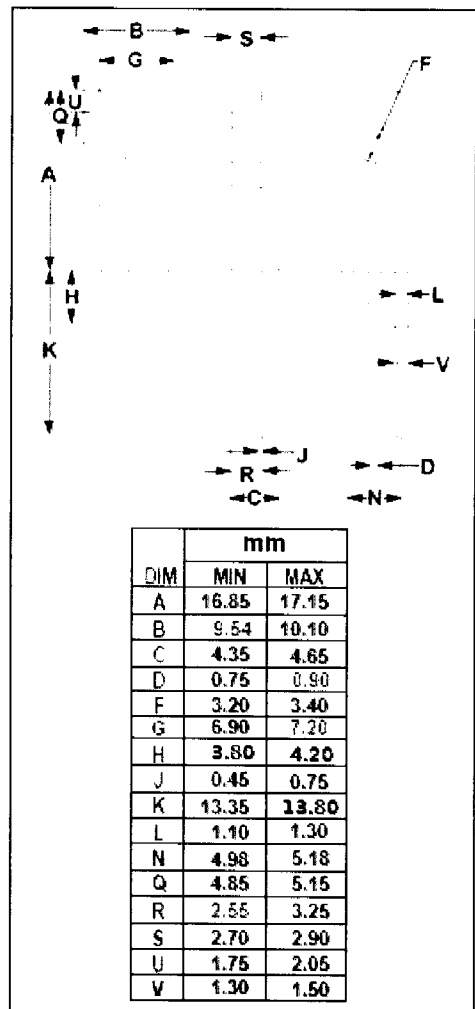
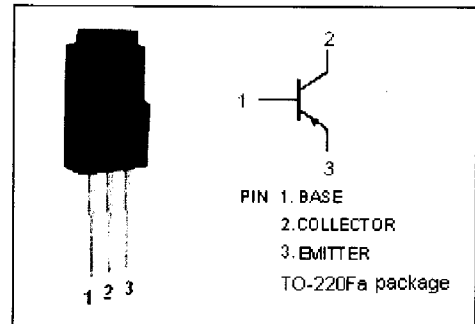
- Low Collector Saturation Voltage-
 : $V_{CE(sat)} = -0.5V(\text{Max.}) @ I_C = -8A$
- High DC Current Gain-
 : $hFE = 70(\text{Min.}) @ I_C = -8A$

APPLICATIONS

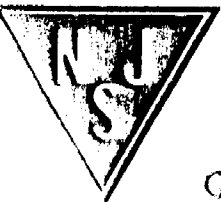
- Strobe flash applications.
- Audio power amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-20	V
V_{EBO}	Emitter-Base Voltage	-8	V
I_C	Collector Current-Continuous	-10	A
I_{CM}	Collector Current-Pulse	-20	A
I_B	Base Current-Continuous	-2	A
P_C	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	2	W
	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	20	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$



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ELECTRICAL CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -10mA; I _B = 0	-20			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -8A; I _B = -0.4A			-0.5	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -8A; V _{CE} = -2V			-1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -50V; I _E = 0			-1.0	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -8V; I _C = 0			-1.0	μ A
h _{FE-1}	DC Current Gain	I _C = -1A; V _{CE} = -2V	100		320	
h _{FE-2}	DC Current Gain	I _C = -8A; V _{CE} = -2V	70			
f _T	Current-Gain—Bandwidth Product	I _C = -1A; V _{CE} = -2V		45		MHz
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = -10V; f= 1MHz		400		pF

◆ h_{FE-1} Classifications

O	Y
100-200	160-320